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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/604,485	07/25/2003	Kun-Chih Lin	ADTP0068USA	1484

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(NAIPC) NORTH AMERICA INTERNATIONAL PATENT OFFICE
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EXAMINER

YOUNG, CHRISTOPHER G

ART UNIT PAPER NUMBER

1756

DATE MAILED: 12/29/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/604,485

Applicant(s)

LIN, KUN-CHIH

Examiner

Christopher G. Young

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
 - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
 - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
 - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 25 July 2003.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-20 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☒ Claim(s) 1-6, 8-17, 19 and 20 is/are allowed.
- 6) ☒ Claim(s) 7 and 18 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 25 July 2003 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
- 1) ☒ Certified copies of the priority documents have been received.
 - 2) ☐ Certified copies of the priority documents have been received in Application No. _____.
 - 3) ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

2. Claims 7 and 18 are rejected under 35 U.S.C. 112, first paragraph, because the specification, while being enabling for using an excimer laser to irradiate the amorphous film, to form a polysilicon film in the first region, does not reasonably provide enablement for the amorphous silicon film in the second region become completely melted and the amorphous silicon film in the first region become partially melted. The specification does not enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the invention commensurate in scope with these claims. The specification describes the amorphous silicon film in the first region being completely melted and the amorphous silicon film on the second region not melted or partially melted.

3. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

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4. Claims 7 and 18 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Each of these claims refers to the laser incorrectly in line 1. The claims call for a "layer", but the term should be "laser". Correction is required.

Allowable Subject Matter

5. Claims 1-6, 8-17, 19 and 20 are allowed.

6. The following is a statement of reasons for the indication of allowable subject matter: The instant application calls for a method of fabricating a polysilicon film by an excimer laser crystallization (ELC) process comprising following steps: providing a substrate, the substrate surface defined with a first region, a second region surrounding the first region, and a third region; forming an amorphous silicon film on the silicon substrate; performing a first photo-etching process to remove parts of the amorphous silicon film in the third region to form an alignment mark in the third region; forming a mask layer on the amorphous silicon film; performing a second photo-etching process to remove the mask layer on the amorphous film in the first region; and performing the excimer laser crystallization process with an excimer laser to make the amorphous film in the first region crystallize to a polysilicon film.

After a search of the relevant prior art areas, the Examiner has cited the most relevant prior art on the attached PTO-892. However, none of the prior art references show the specific combination of features as claimed. The teachings of Harkin et al. and Lin show the basic features of the instant application except for the designation of a third region on the substrate, and all of the associated processing of the third region to form an alignment mark. The prior art does not contemplate any of these processing steps.

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. The Examiner has set forth the reason for indicating allowable subject matter above. The following are the basic teachings of the art cited by the Examiner.

Harkin et al. teaches a method of forming a polysilicon film by an excimer laser crystallization process (Abstract). Harkin et al. shows providing a substrate (having a buffer layer) defined with a first region and a second region (Fig. 1-2, col. 7, lines 1-25, col. 10, lines 1-10). Harkin et al. discloses forming an amorphous silicon film on the substrate, forming a mask layer on the amorphous silicon film, performing a first photo-etching process to remove the mask layer on the first region (Fig. 3-5, 13-14, col. 5, lines 50-65 col. 6, lines 1-20, col. 7, lines 24-67, col. 12, lines 49-67, col. 13, lines 1-17).

Harkin et al. teaches forming a heat-retaining capping layer covering the mask layer and the amorphous silicon film (Fig. 3-5, col. 7, lines 40-67). Furthermore, Harkin

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et al. shows performing the excimer laser crystallization process to make the amorphous silicon film in the first region crystallize to a polysilicon film (Fig. 5, col. 6, lines 1-20, col. 8, lines 9-25). Harkin et al. discloses an etching process to remove the heat-retaining layer, the mask layer, and to etch the portions of the amorphous film after forming the polysilicon film (Fig. 13-14, col. 4, lines 24-35, col.9, lines 40-45, col. 13, lines 1-17). Harkin et al. teaches the mask layer and the heat-retaining capping layer comprising silicon oxide, silicon nitride, silicon oxynitride or a metal (col. 3, lines 47-50, 63-67, col. 4, lines 1-4).

Kawasaki et al. teaches the excimer laser having a period from several nanoseconds through several hundred nanoseconds (col. 4, lines 58-67).

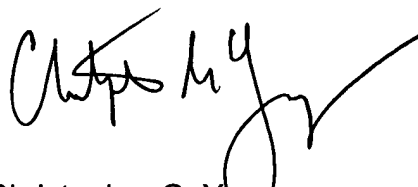
Conclusion

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Christopher G. Young whose telephone number is 571-272-1394. The examiner can normally be reached on Monday-Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark Huff can be reached on 571-272-1385. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

A handwritten signature in black ink, appearing to read 'Christopher G. Young', with a large, sweeping flourish at the end.

Christopher G. Young
Primary Examiner
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cgy